

BAS19L, BAS20L, BAS21L, BAS21DW5

High Voltage Switching Diode

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	120 200 250	Vdc
Repetitive Peak Reverse Voltage	V_{RRM}	120 200 250	Vdc
Continuous Forward Current	I_F	200	mAdc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I_{FSM}	2	A
Repetitive Peak Forward Current (Pulse Train: $T_{ON} = 1$ s, $T_{OFF} = 0.5$ s)	I_{FRM}	0.6	A
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Power Dissipation (Note 1)	P_D	385	mW
Electrostatic Discharge	ESD	HM < 500 MM < 400	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

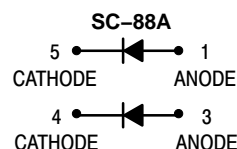
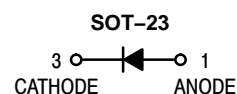
1. Mounted on FR-5 Board = 1.0 x 0.75 x 0.062 in.



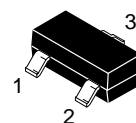
ON Semiconductor®

www.onsemi.com

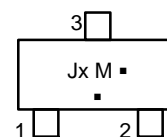
HIGH VOLTAGE SWITCHING DIODE



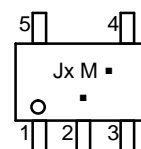
MARKING DIAGRAMS



SOT-23 (TO-236)
CASE 318
STYLE 8



SC-88A (SOT-353)
CASE 419A



x = P, R, or S
P = BAS19L
R = BAS20L
S = BAS21L or BAS21DW5
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon the manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

BAS19L, BAS20L, BAS21L, BAS21DW5

Thermal Characteristics (SOT-23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 3) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics (SC-88A)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P_D	385	mW
Thermal Resistance – Junction-to-Ambient Derate Above 25°C	$R_{\theta JA}$	328	$^\circ\text{C/W}$
		3.0	mW/ $^\circ\text{C}$
Maximum Junction Temperature	T_{Jmax}	150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

2. FR-5 = 1.0 × 0.75 × 0.062 in.

3. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

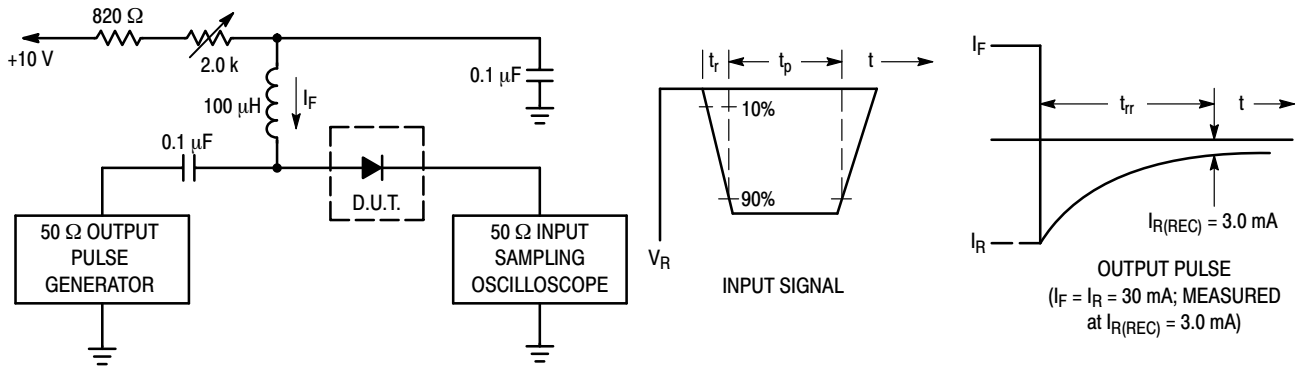
4. Mounted on FR-5 Board = 1.0 × 0.75 × 0.062 in.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
Reverse Voltage Leakage Current ($V_R = 100\text{ Vdc}$) ($V_R = 150\text{ Vdc}$) ($V_R = 200\text{ Vdc}$) ($V_R = 100\text{ Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 150\text{ Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 200\text{ Vdc}, T_J = 150^\circ\text{C}$)	I_R	-	0.1	μAdc	
			BAS19	0.1	
			BAS20	0.1	
			BAS21	100	
			BAS19	100	
			BAS20	100	
Reverse Breakdown Voltage ($I_{BR} = 100\ \mu\text{Adc}$) ($I_{BR} = 100\ \mu\text{Adc}$) ($I_{BR} = 100\ \mu\text{Adc}$)	$V_{(BR)}$	-	120	Vdc	
			BAS19	200	
			BAS20	250	
Forward Voltage ($I_F = 100\text{ mAdc}$) ($I_F = 200\text{ mAdc}$)	V_F	-	1.0	Vdc	
			BAS19	1.25	
Diode Capacitance ($V_R = 0, f = 1.0\text{ MHz}$)	C_D	-	5.0	pF	
Reverse Recovery Time ($I_F = I_R = 30\text{ mAdc}, I_{R(REC)} = 3.0\text{ mAdc}, R_L = 100$)	t_{rr}	-	50	ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BAS19L, BAS20L, BAS21L, BAS21DW5



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

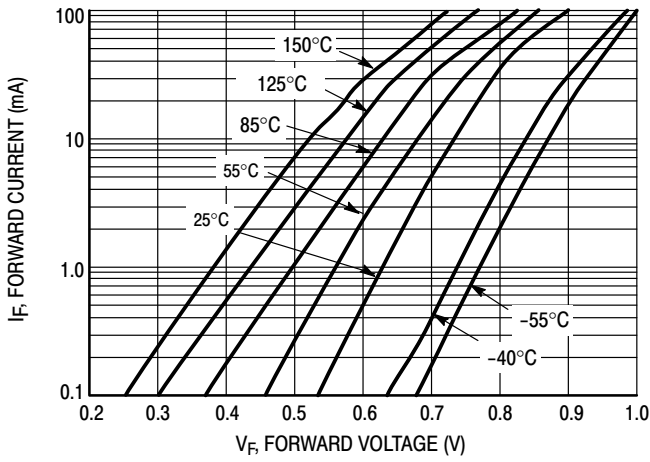


Figure 2. V_F vs. I_F

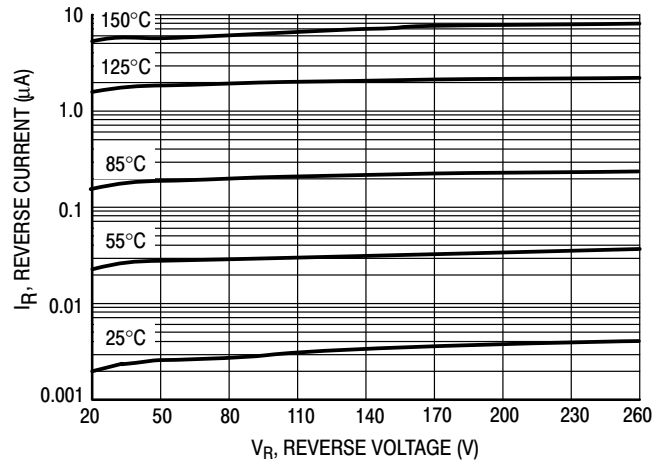


Figure 3. I_R vs. V_R

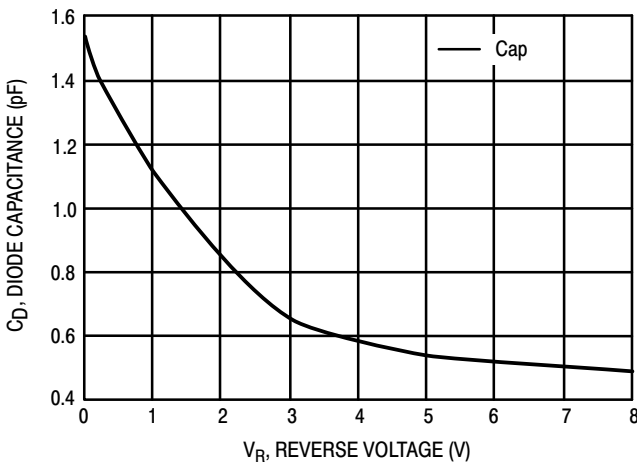


Figure 4. Capacitance

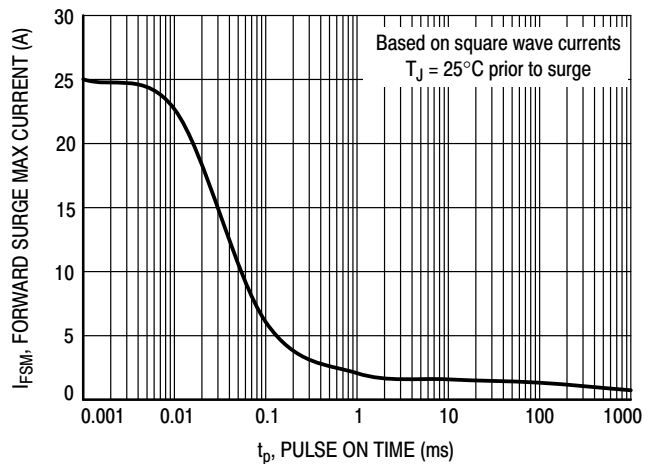


Figure 5. Forward Surge Current

BAS19L, BAS20L, BAS21L, BAS21DW5

ORDERING INFORMATION

Device	Package	Shipping†
BAS19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS19LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS20LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SBAS21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS21LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
BAS21DW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T1G*	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T3G*	SC-88A (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- | | | | |
|---|---|---|--|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE |
| STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE | STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE |
| STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE |
| STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION | STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE |

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236)	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



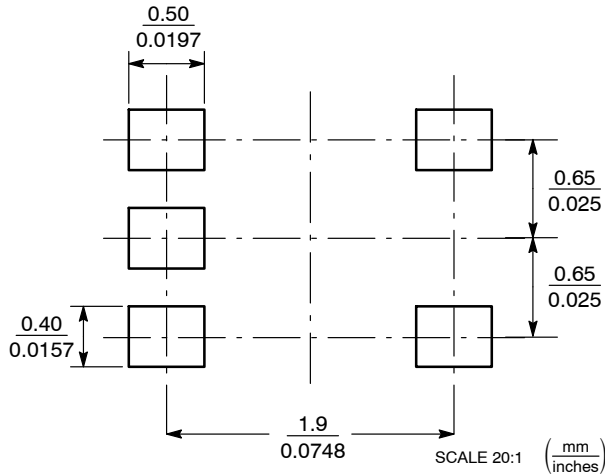
SCALE 2:1

SC-88A (SC-70-5/SOT-353)
CASE 419A-02
ISSUE L

DATE 17 JAN 2013



SOLDER FOOTPRINT

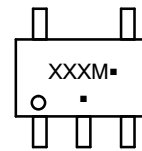


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- | | | | | |
|--|--|--|--|--|
| <p>STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR</p> | <p>STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE</p> | <p>STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1</p> | <p>STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2</p> | <p>STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4</p> |
| <p>STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1</p> | <p>STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR</p> | <p>STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER</p> | <p>STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE</p> | <p>Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.</p> |

DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-88A (SC-70-5/SOT-353)	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative